

Silicon PNP Power Transistors

2SB1009

DESCRIPTION

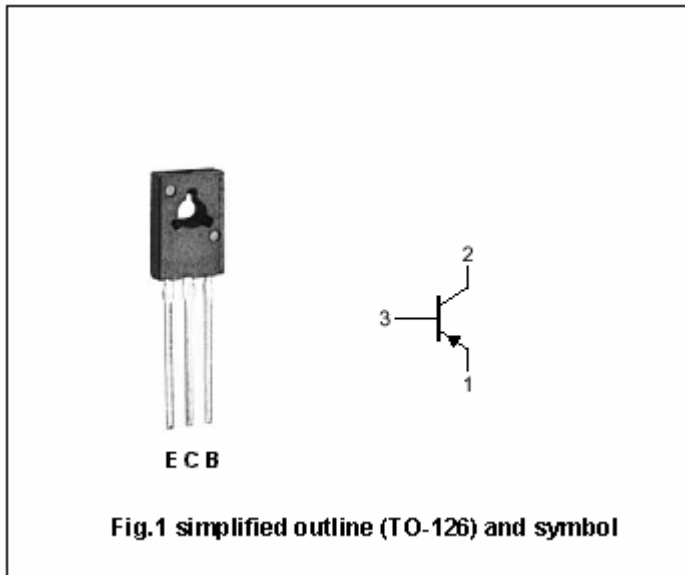
- With TO-126 package
- Complement to type 2SD1380

APPLICATIONS

- For use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-40	V
V_{CEO}	Collector-emitter voltage	Open base	-32	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-2	A
P_D	Total power dissipation	$T_a=25$	0.1	W
		$T_C=25$	10	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-32			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2.0A; I _B =-0.2A			-0.8	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2.0A ; I _B =-0.2A			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-20V; I _E =0			-1	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-3V; I _C =0			-1	μ A
h _{FE-1}	DC current gain	I _C =-20mA ; V _{CE} =-5V	40			
h _{FE-2}	DC current gain	I _C =-500mA ; V _{CE} =-5V	82		390	
f _T	Transition frequency	I _C =-500mA ; V _{CE} =-5V		100		MHz
C _{OB}	Collector output capacitance	f=1MHz ; V _{CB} =-10V		50		pF

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PACKAGE OUTLINE

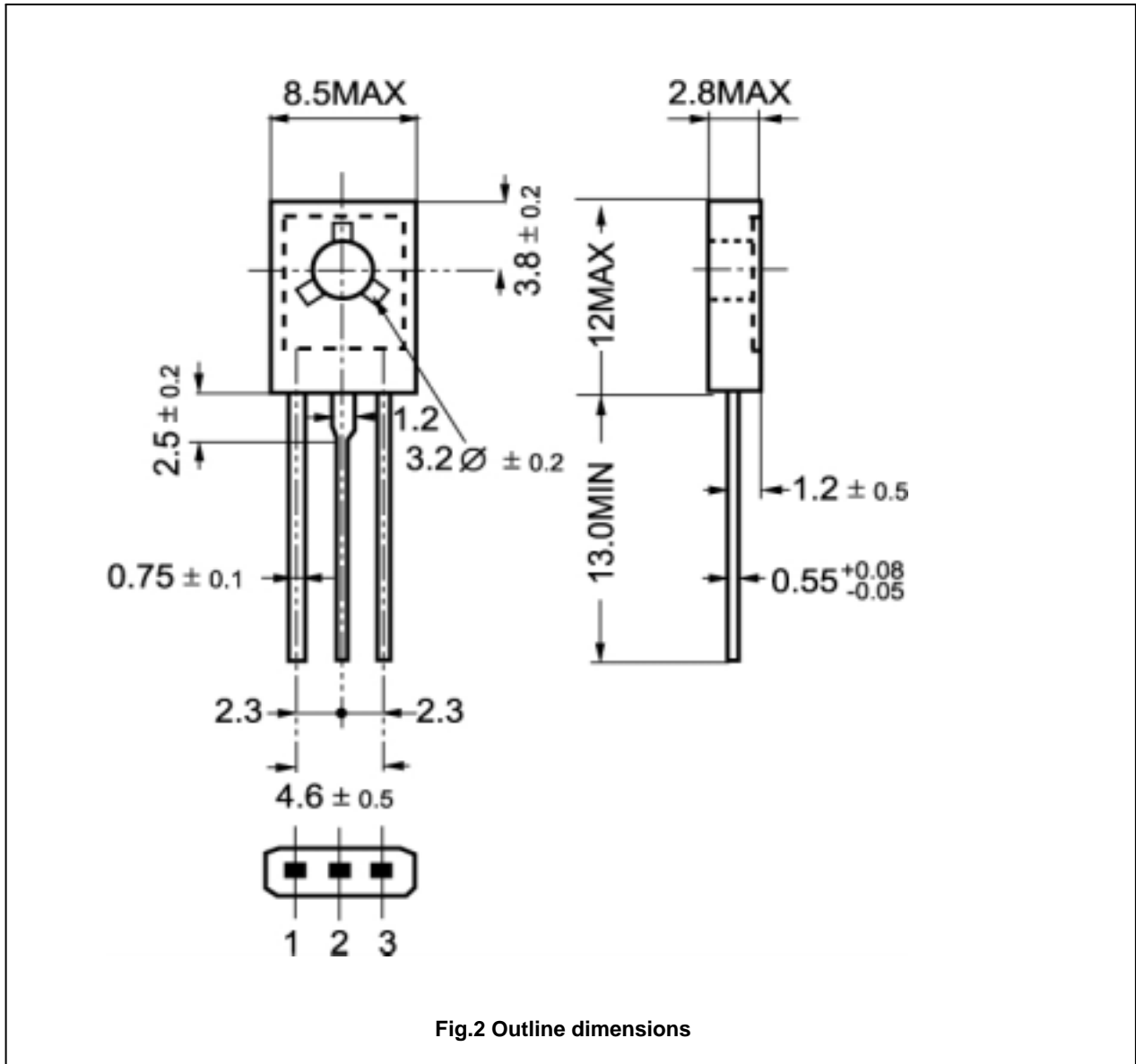


Fig.2 Outline dimensions